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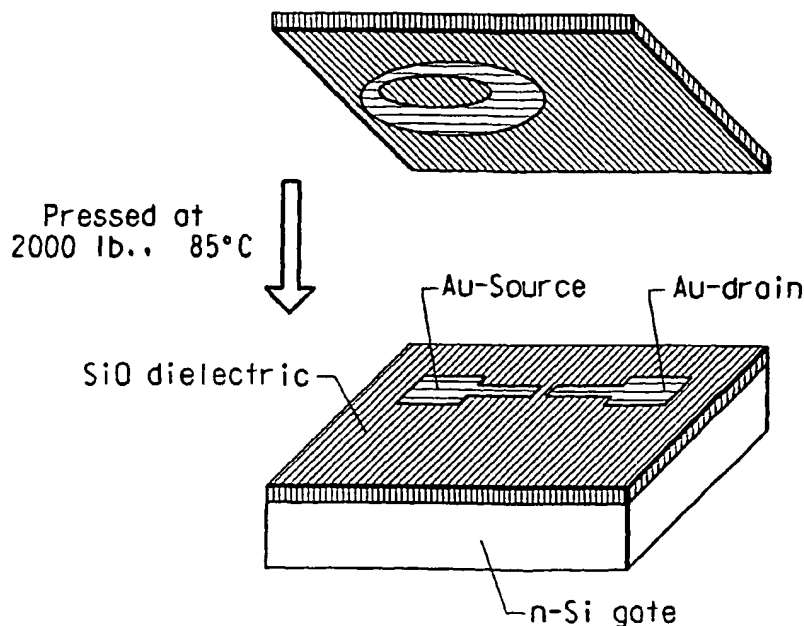
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(54) Title: LAMINATION OF ORGANIC SEMICONDUCTORS



(57) Abstract: Low temperature, ambient pressure processes are desired for fabrication of transistors on flexible polymer substrates. Lamination of semiconductors is such a process. The semiconductor is deposited on a donor substrate. The donor is positioned over a receiver substrate, which may be patterned with additional transistor elements. The semiconductor is transferred from the donor to the receiver by lamination.

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